



<b>Title of Change:</b>	NCP81239 Datasheet update		
<b>Effective date:</b>	16 November 2016		
<b>Contact information:</b>	Contact your local ON Semiconductor Sales Office or <Joe.Chong@onsemi.com>		
<b>Type of notification:</b>	ON Semiconductor will consider this change accepted.		
<b>Change category:</b>	<input type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input checked="" type="checkbox"/> Other <u>Datasheet Update</u>		
<b>Change Sub-Category(s):</b>	<input type="checkbox"/> Manufacturing Site Change/Addition <input type="checkbox"/> Manufacturing Process Change	<input type="checkbox"/> Material Change <input type="checkbox"/> Product specific change	<input checked="" type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Shipping/Packaging/Marking <input type="checkbox"/> Other: _____
<b>Sites Affected:</b>	<input type="checkbox"/> All site(s) <input checked="" type="checkbox"/> not applicable <input type="checkbox"/> ON Semiconductor site(s) : <input type="checkbox"/> External Foundry/Subcon site(s)		
<b>Description and Purpose:</b>			
ON Semiconductor has updated the NCP81239MNTXG data sheet with the latest version. Latest datasheet can be downloaded from <a href="http://www.onsemi.com">www.onsemi.com</a>  Specific changes are shown on page 2.			



Parameter	Symbol	Test Conditions	From				To			
			Min	Typ	Max	Units	Min	Typ	Max	Units
VCC UVLO Rising Threshold	VCC <sub>START</sub>			4.16		V		4.3		V
UVLO Hysteresis for VCC	VCCV <sub>HYS</sub>	Falling Hysteresis		200		mV		300		mV
VDRV UVLO Rising Threshold	VRDV <sub>START</sub>			4.16		V		4.3		V
UVLO Hysteresis for VDRV	VDRV <sub>HYS</sub>	Falling Hysteresis		200		mV		300		mV
VCC Output Voltage	VCC	With no external load	4.9	5		V	4.5	5		V
VDRIVE Switching Current Buck	IV1_SW	EN = 5, Cgate = 2.2 nF, VSW = 0 V FSW = 600 kHz, Comp = 1 V		12		mA		15		mA
VDRIVE Switching Current Boost	IV1_SW	EN = 5, Cgate = 2.2 nF, VSW = 0 V FSW = 600 kHz, Comp = 1 V		12		mA		15		mA
Voltage Accuracy Over Temperature	VOUERT	VFB < 0.5 V	-3.3			3 %	-5			5 mV
	VOUTER	TA = 25°C VFB > 0.5 V	-0.35			0.35 %	-0.45			0.45 %
Forward Voltage Drop	VFBOT	IF = 10 mA, TA = 25°C	0.42	0.46	0.51	V	0.35	0.46	0.55	V
Reverse Bias Leakage Current	DIL	BST-VSW = 5 V VSW = 28 V, TA = 25°C		0.05	0.16	µA		0.05	1	µA
Oscillator Frequency	FSW_0	FSW = 000, default	540	600	660	kHz	528	600	672	kHz
	FSW_1	FSW = 001	135	150	166	kHz	132	150	168	kHz
	FSW_7	FSW = 110	1058	1200	1320	kHz	1056	1200	1344	kHz
Oscillator Frequency Accuracy	FSWE		-12			10 %	-12			12 %
Interrupt Low Voltage	VINTI	IINT(sink) = 2 mA			0.04	V			0.2	V
Interrupt High Leakage Current	INII	3.3V		3	11	nA		3	100	nA
FB Overvoltage Threshold	FB_OV			116		%		120		%
Current Limit Indicator Output Low	CLINDL	Input current = 500 µA		5.6	10	mV		5.6	100	mV
Internal Current Sense Gain for PWM	ICG	CSPx-CSNx = 100 mV	9.3	9.8	10.42	V/V	9.2	9.8	10.5	V/V
Pull Down Delay	CFETD	Measured at 10% to 90% of VCC, -40°C < TA < 100°C		1.3		mS		10		mS
Dead Battery Output Voltage	VIO	VDB = 5 V, -40°C < TA < 100°C Output Current 32 mA	4.4	4.7	4.77	V	4	4.7	5	V
EN High Threshold Voltage	ENHT	EM_MASK = ENPU = ENPOL = 0		798	808	mV		798	820	mV
EN Low Threshold Voltage	ENLT		652	665		mV	640	665		mV
Communication Speed	I2CSP		0.4		1	MHz			1	MHz

List of affected Standard Parts:

NCP81239MNTXG